

2SJ245 L, 2SJ245 S

SILICON P-CHANNEL MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V Gate drive device can be driven from 5 V source
- Suitable for Switching regulator, DC – DC converter

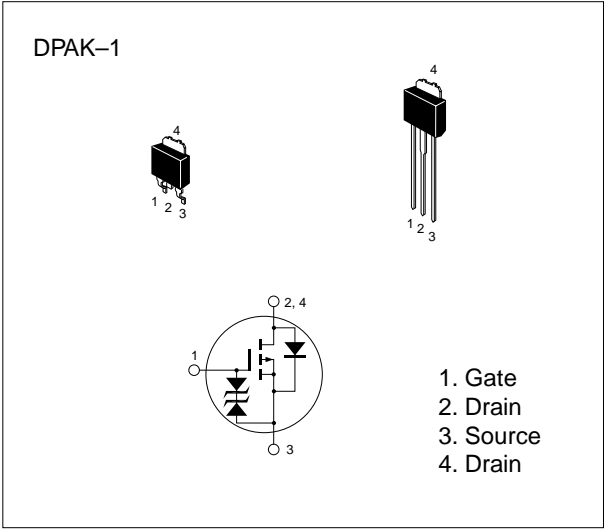


Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	–60	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	–5	A
Drain peak current	$I_{D(pulse)}^*$	–20	A
Body–drain diode reverse drain current	$I_{DR}$	–5	A
Channel dissipation	$P_{ch}^{**}$	20	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	–55 to +150	°C

\*  $PW \leq 10 \mu s$ , duty cycle  $\leq 1 \%$

\*\* Value at  $T_c=25^\circ C$

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-100	$\mu\text{A}$	$V_{DS} = -50 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}$ , $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.2	0.25	$\Omega$	$I_D = -3 \text{ A}$ $V_{GS} = -10 \text{ V}^*$
		—	0.28	0.38	$\Omega$	$I_D = -3 \text{ A}$ $V_{GS} = -4 \text{ V}^*$
Forward transfer admittance	$ y_{fs} $	2.2	3.7	—	S	$I_D = -3 \text{ A}$ $V_{DS} = -10 \text{ V}^*$
Input capacitance	$C_{iss}$	—	610	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	$C_{oss}$	—	315	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	95	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	12	—	ns	$I_D = -3 \text{ A}$
Rise time	$t_r$	—	45	—	ns	$V_{GS} = -10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	170	—	ns	$R_L = 10 \text{ }\Omega$
Fall time	$t_f$	—	90	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	-1.1	—	V	$I_F = -5 \text{ A}$ , $V_{GS} = 0$
Body-drain diode reverse recovery time	$t_{rr}$	—	160	—	ns	$I_F = -5 \text{ A}$ , $V_{GS} = 0$ , $di_F / dt = 50 \text{ A} / \mu\text{s}$

